# P-Channel Enhancement-Mode Vertical DMOS FET

## Features

- Low threshold (-2.0V max.)
- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

## Applications

- Logic level interfaces - ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

## General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## Ordering Information

| Part Number | Package Option | Packing |
|---|---|---|
| TP2635N3-G | 3-Lead TO-92 | 1000/Bag |
| TP2635N3-G P002 | 3-Lead TO-92 | 2000/Reel |
| TP2635N3-G P003 | | |
| TP2635N3-G P005 | | |
| TP2635N3-G P013 | | |
| TP2635N3-G P014 | | |

*-G denotes a lead (Pb)-free / RoHS compliant package.*
*Contact factory for Wafer / Die availablity.*
*Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.*

## Product Summary

| $BV_{DSS}/BV_{DGS}$ | $R_{DS(ON)}$ (max) | $I_{D(ON)}$ (min) | $V_{GS(th)}$ (max) |
|---|---|---|---|
| -350V | 15Ω | -2.0A | -0.7V |

## Pin Configuration


**TO-92**

## Absolute Maximum Ratings

| Parameter | Value |
|---|---|
| Drain-to-source voltage | $BV_{DSS}$ |
| Drain-to-gate voltage | $BV_{DGS}$ |
| Gate-to-source voltage | ±20V |
| Operating and storage temperature | -55°C to +150°C |

*Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.*

## Product Marking


YY = Year Sealed
WW = Week Sealed
_____ = "Green" Packaging

*Package may or may not include the following marks: Si or* 

**TO-92**

## Typical Thermal Resistance

| Package | $\theta_{ja}$ |
|---|---|
| TO-92 | 132°C/W |

## Thermal Characteristics

| Package | $I_D$ (continuous)† | $I_D$ (pulsed) | Power Dissipation @$T_A$ = 25°C | $I_{DR}$ † | $I_{DRM}$ |
|---|---|---|---|---|---|
| TO-92 | -180mA | -800mA | 1.0W | -180mA | -800mA |

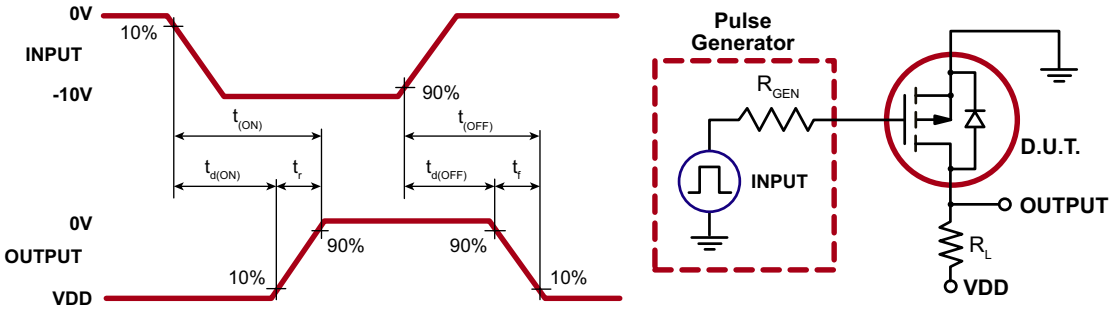
***Notes:***
† $I_D$ *(continuous) is limited by max rated* $T_j$ .

## Electrical Characteristics *($T_A$ = 25°C unless otherwise specified)*

| Sym | Parameter | Min | Typ | Max | Units | Conditions |
|---|---|---|---|---|---|---|
| $BV_{DSS}$ | Drain-to-source breakdown voltage | -350 | - | - | V | $V_{GS}$ = 0V, $I_D$ = -2.0mA |
| $V_{GS(th)}$ | Gate threshold voltage | -0.8 | - | -2.0 | V | $V_{GS}$ = $V_{DS}$, $I_D$ = -1.0mA |
| $\Delta V_{GS(th)}$ | Change in $V_{GS(th)}$ with temperature | - | - | 5 | mV/°C | $V_{GS}$ = $V_{DS}$, $I_D$ = -1.0mA |
| $I_{GSS}$ | Gate body leakage | - | | -100 | nA | $V_{GS}$ = ±20V, $V_{DS}$ = 0V |
| $I_{DSS}$ | Zero gate voltage drain current | - | - | -1.0 | μA | $V_{GS}$ = 0V, $V_{DS}$ = -100V |
| | | | | -10.0 | | $V_{GS}$ = 0V, $V_{DS}$ = Max rating |
| | | | | -1.0 | mA | $V_{DS}$ = 0.8 Max Rating, $V_{GS}$ = 0V, $T_A$ = 125°C |
| $I_{D(ON)}$ | On-state drain current | -0.7 | - | - | A | $V_{GS}$ = -10V, $V_{DS}$ = -25V |
| $R_{DS(ON)}$ | Static drain-to-source on-state resistance | - | 12 | 15 | Ω | $V_{GS}$ = -2.5V, $I_D$ = -20mA |
| | | | 11 | 15 | | $V_{GS}$ = -4.5V, $I_D$ = -150mA |
| | | | 11 | 15 | | $V_{GS}$ = -10V, $I_D$ = -300mA |
| $\Delta R_{DS(ON)}$ | Change in $R_{DS(ON)}$ with temperature | - | - | 0.75 | %/°C | $V_{GS}$ = -10V, $I_D$ = -300mA |
| $G_{FS}$ | Forward transconductance | 200 | - | - | mmho | $V_{DS}$ = -25V, $I_D$ = -300mA |
| $C_{ISS}$ | Input capacitance | - | - | 300 | pF | $V_{GS}$ = 0V, $V_{DS}$ = -25V, f = 1.0MHz |
| $C_{OSS}$ | Common source output capacitance | - | - | 50 | | |
| $C_{RSS}$ | Reverse transfer capacitance | - | - | 12 | | |
| $t_{d(ON)}$ | Turn-on delay time | - | - | 10 | ns | $V_{DD}$ = -25V, $I_D$ = -300mA, $R_{GEN}$ = 25Ω |
| $t_r$ | Rise time | - | - | 15 | | |
| $t_{d(OFF)}$ | Turn-off delay time | - | - | 60 | | |
| $t_f$ | Fall time | - | - | 40 | | |
| $V_{SD}$ | Diode forward voltage drop | - | - | -1.8 | V | $V_{GS}$ = 0V, $I_{SD}$ = -200mA |
| $t_{rr}$ | Reverse recovery time | - | 300 | - | ns | $V_{GS}$ = 0V, $I_{SD}$ = -200mA |

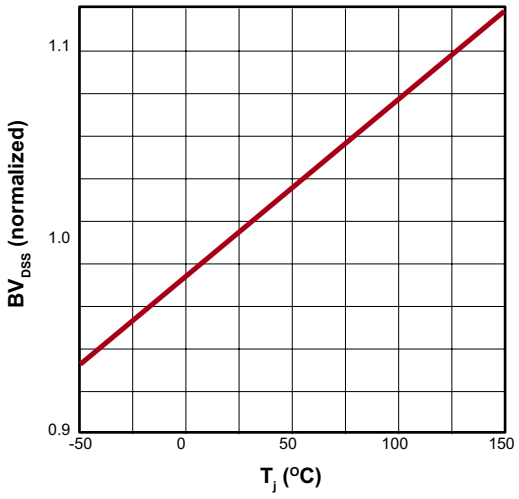
***Notes:***
1. *All D.C. parameters 100% tested at 25C unless otherwise stated. (Pulse test: 300s pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

## N- Channel Switching Waveforms and Test Circuit

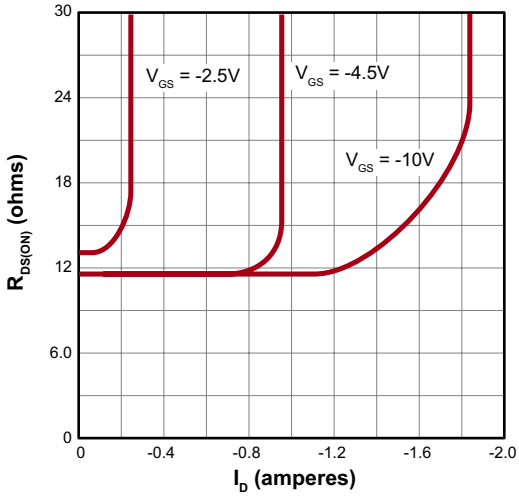


## Typical Performance Curves

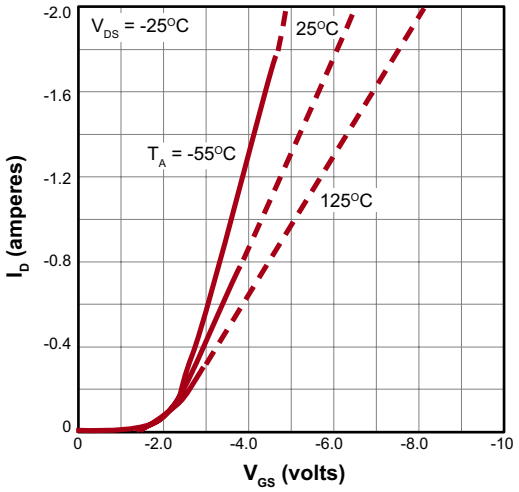
### $BV_{DSS}$ Variation with Temperature



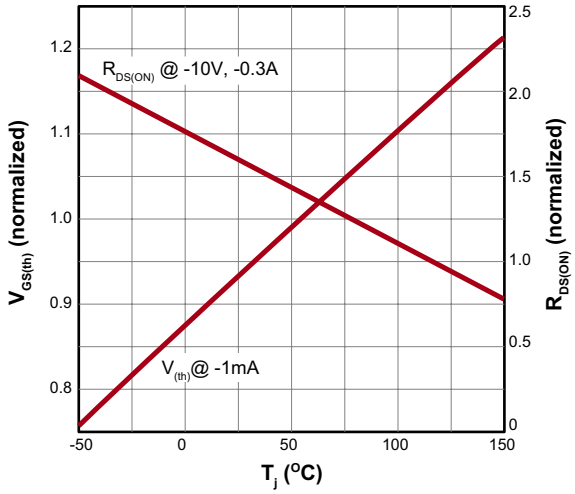

### On-Resistance vs. Drain Current



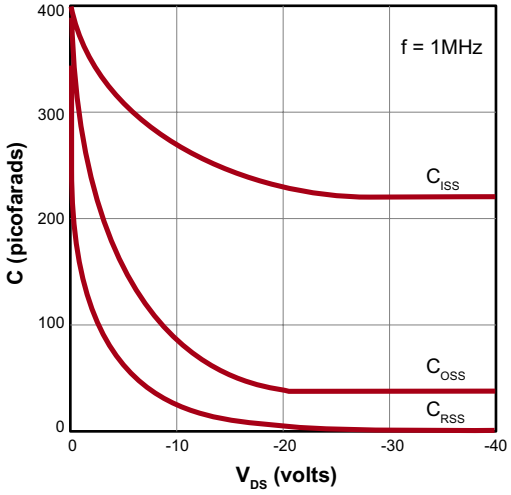

### Transfer Characteristics



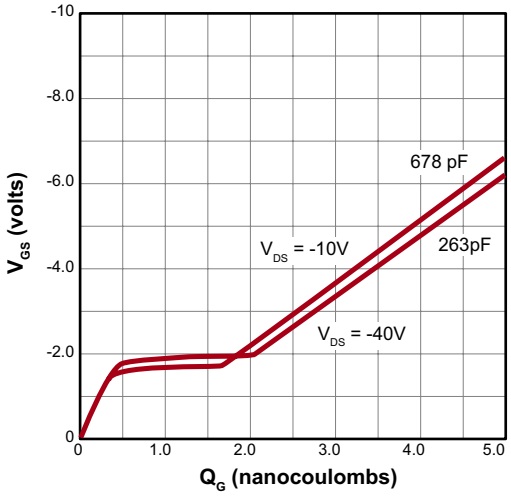

### $V_{(th)}$ and $R_{DS}$ Variation with Temperature




### Capacitance vs. Drain-to-Source Voltage

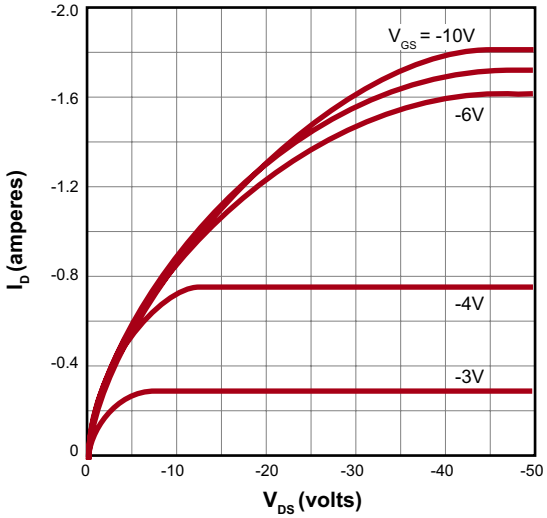



### Gate Drive Dynamic Characteristics

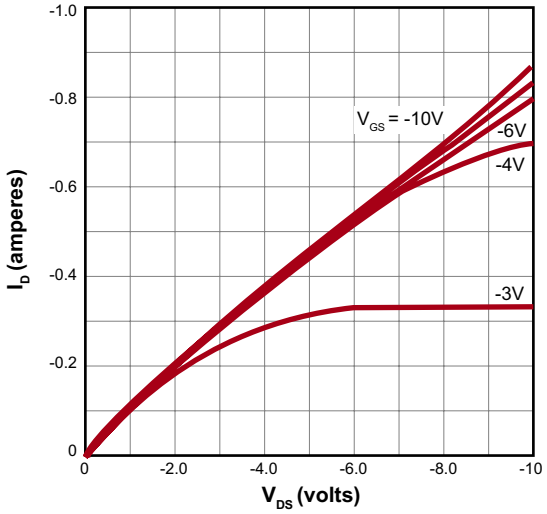


## Typical Performance Curves (cont.)

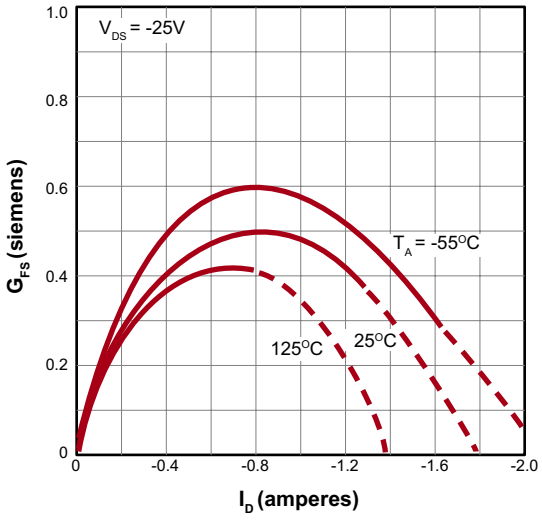
### Output Characteristics



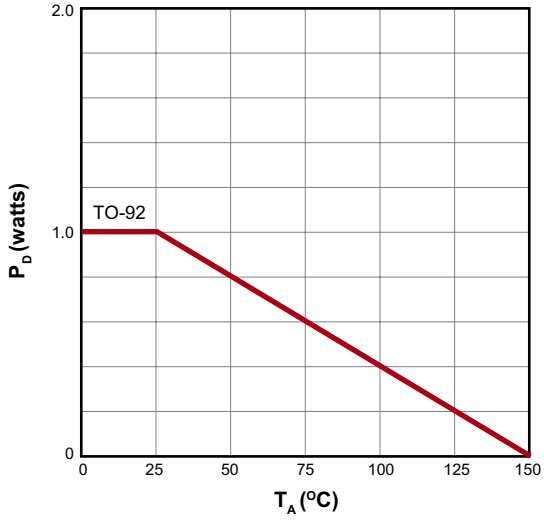

### Saturation Characteristics



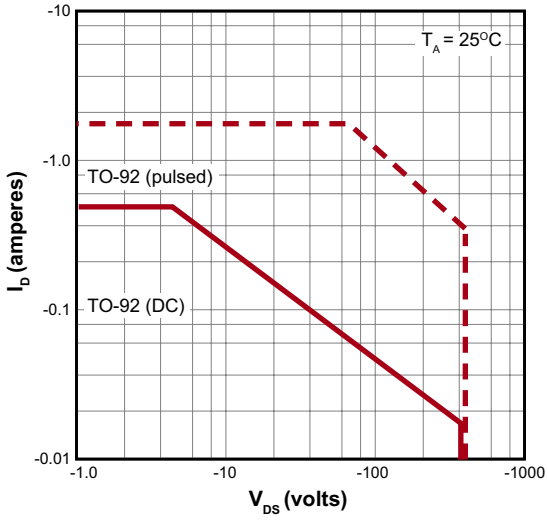

### Transconductance vs. Drain Current



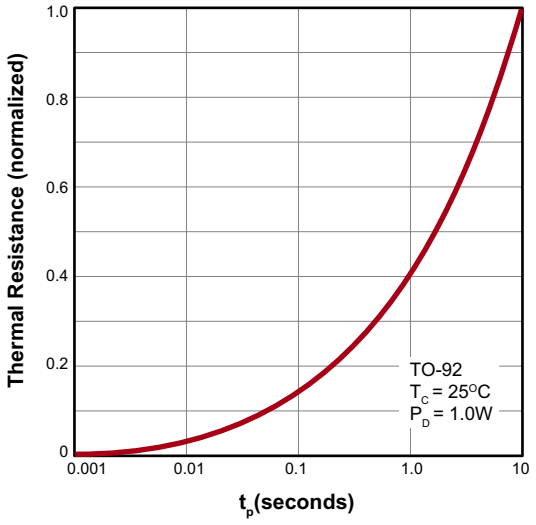

### Power Dissipation vs. Temperature



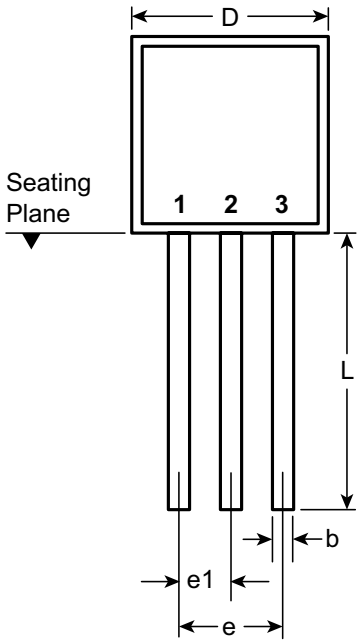

### Maximum Rated Safe Operating Area



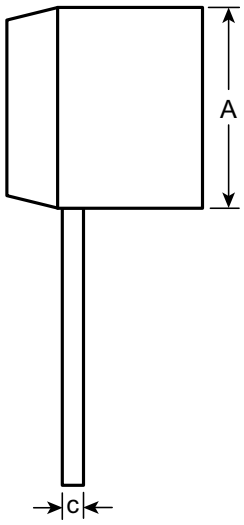

### Thermal Response Characteristics



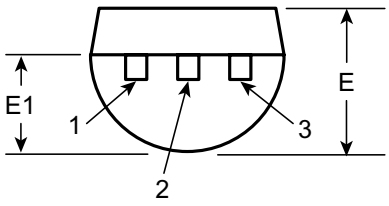
# 3-Lead TO-92 Package Outline (N3)




**Front View**




**Side View**




| Symbol | | A | b | c | D | E | E1 | e | e1 | L |
|---|---|---|---|---|---|---|---|---|---|---|
| Dimensions (inches) | MIN | .170 | .014† | .014† | .175 | .125 | .080 | .095 | .045 | .500 |
| | NOM | - | - | - | - | - | - | - | - | - |
| | MAX | .210 | .022† | .022† | .205 | .165 | .105 | .105 | .055 | .610* |

*JEDEC Registration TO-92.*
** This dimension is not specified in the JEDEC drawing.*
*† This dimension differs from the JEDEC drawing.*
***Drawings not to scale.***
***Supertex Doc.#:** DSPD-3TO92N3, Version E041009.*

*(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)*



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